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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/528,296	03/17/2000	Kazuhiko Takada	000294	4124
23850	7590 03/14/2003			
ARMSTRONG, WESTERMAN & HATTORI, LLP			EXAMINER	
1725 K STREET, NW SUITE 1000 WASHINGTON, DC 20006		NADAV, ORI		
			ART UNIT	PAPER NUMBER
			2811	

Please find below and/or attached an Office communication concerning this application or proceeding.

		- In			
	Application N .	Applicant(s)			
,	09/528,296	TAKADA, KAZUHIKO			
Offic Action Summary	Examiner	Art Unit			
	ori nadav	2811			
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply					
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.  - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.  - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).  - Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).  Status					
1) Responsive to communication(s) filed on 30 J	<u>anuary 2003</u> .				
2a)☐ This action is <b>FINAL</b> . 2b)⊠ Thi	is action is non-final.				
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.					
Disposition of Claims					
4)⊠ Claim(s) <u>1-4 and 7-12</u> is/are pending in the application.					
4a) Of the above claim(s) <u>8-12</u> is/are withdrawn from consideration.					
5) Claim(s) is/are allowed.					
6)⊠ Claim(s) <u>1-4 and 7</u> is/are rejected.					
7) Claim(s) is/are objected to.					
8) Claim(s) are subject to restriction and/or election requirement.  Application Papers					
9)☐ The specification is objected to by the Examiner.					
10) ☐ The drawing(s) filed on is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.					
Applicant may not request that any objection to the	e drawing(s) be held in abeyance. S	ee 37 CFR 1.85(a).			
11)☐ The proposed drawing correction filed on is: a)☐ approved b)☐ disapproved by the Examiner.					
If approved, corrected drawings are required in reply to this Office action.					
12)☐ The oath or declaration is objected to by the Examiner.					
Pri rity under 35 U.S.C. §§ 119 and 120					
13) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).					
a) ☐ All b) ☐ Some * c) ☐ None of:					
1. Certified copies of the priority documents have been received.					
2. Certified copies of the priority documents have been received in Application No					
<ul> <li>3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).</li> <li>* See the attached detailed Office action for a list of the certified copies not received.</li> </ul>					
14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).					
a) ☐ The translation of the foreign language provisional application has been received. 15)☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.					
Attachment(s)					
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449) Paper No(s)	5) Notice of Informal	y (PTO-413) Paper No(s) Patent Application (PTO-152)			
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## **DETAILED ACTION**

## Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which the subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1-4 and 7 are rejected under 35 U.S.C. 103(a) as being unpatentable over Admitted Prior Art (APA) in view of Cook et al. (6,022,791) and Chiang et al. (5,817,572).

Regarding claim 6, APA teaches in figure 2 and related text (pages 1-3) a substrate 21; and a multilayer interconnection structure formed on the substrate (page 1, lines 15-37), the multilayer interconnection structure including: at least first and second interlayer insulation films 24, 25 provided on the substrate; and a guard ring pattern 12 embedded in each of the first and second interlayer insulation films, the guard ring pattern extending along a periphery of the substrate (figure 1B), the multilayer interconnection structure being planarized by using a CMP process (page 5, 11-17),

the guard ring pattern including: a groove 24A formed in each of the first and second interlayer insulation films, a conductive wall 24C filling the groove in each of the first and second interlayer insulation films 24, 25 and extending to a top principal surface thereof; and

a conductive pattern 25A making a contact with a top part of the conductive wall 24C and having a principal surface coincident to the top principal surface of the interlayer insulation film 24, the conductive wall 24C in the first interlayer insulation film 24 being offset with respect to the conductive wall 25C in the second interlayer insulation film 25 in a direction parallel to a principal surface of the substrate when viewed in a direction perpendicular to the principal surface of the substrate, wherein the interlayer insulation film comprises a first insulation film 24 that support the conductive wall 24C, the conductive pattern comprising Cu (page 4, line 28 to page 5, line 17).

APA does not teach a guard ring pattern having a groove and a conductive wall comprising Cu and changing direction repeatedly and alternatively in a plane parallel to the substrate in one of a triangular wave pattern and a rectangular wave pattern, wherein the conductive wall extends from a bottom principal surface of the interlayer insulation film and a second insulation film that supports the conductive pattern laterally.

Cook et al. teach in figures 5 and 8 and related text a guard ring pattern 60, 70, respectively having a groove and a conductive wall M0-M4 changing direction repeatedly and alternatively in a plane parallel to the substrate in one of a triangular wave pattern and a rectangular wave pattern (column 4, lines 7-13).

The claimed limitations of a conductive wall extending from a bottom principal surface of the interlayer insulation film and a second insulation film supporting the conductive pattern laterally are not taught by APA, because APA does not form the conductive structure using etch stop layers. Chiang et al. teach in figure 25 and related text forming a

conductive structure using etch stop layers. Chiang et al. teach a conductive layer 393, 394 (column 21, line 25) extends from a bottom principal surface of the interlayer insulation film 391 to a top principal surface thereof, and a second insulation film 323 (an etch stop layer) that supports conductive pattern 360, 361 laterally.

It would have been obvious to a person of ordinary skill in the art at the time the invention was made to use a guard ring pattern having a groove and a conductive wall comprising Cu and changing direction repeatedly and alternatively in a plane parallel to the substrate in one of a triangular wave pattern and a rectangular wave pattern, as taught by Cook et al., and a conductive wall extends from a bottom principal surface of the interlayer insulation film, as taught by Chiang et al., in APA's device in order to reduce stress and prevent cracks, to improve the problems of signal delay in the device, and in order to provide better control over the depth of the conductive wall and to avoid additional planarizing steps, respectively. The combination is motivated by the teachings of Cook et al. who point out the advantages of using a guard ring pattern having a groove and a conductive wall changing direction repeatedly and alternatively in a plane parallel to the substrate in one of a triangular wave pattern and a rectangular wave pattern with respect to a guard ring pattern having a straight pattern (column 4, lines 14-24), and by the teachings of Chiang et al. who point out the advantages of forming a conductive wall extending from a bottom principal surface of the interlayer insulation film to a top principal

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surface thereof by using an etch stop layer in between the two interlayer insulation films

(column 3, lines 21-35).

Note that although APA teaches a multilayer interconnection structure being planarized by

using a CMP process (page 5, 11-17) this is a process limitation which would not carry

patentable weight in this claim drawn to a structure, because distinct structure is not

necessarily produced. A "product by process" claim is directed to the product per se,

no matter how actually made, In re Hirao, 190 USPQ 15 at 17 (footnote 3). See also In

re Brown, 173 USPQ 685; In re Luck, 177 USPQ 523; In re Fessmann, 180 USPQ 324;

In re Avery, 186 USPQ 161; In re Wertheim, 191 USPQ 90 (209 USPQ 554 does not

deal with this issue); and In re Marosi et al., 218 USPQ 289, all of which make it clear

that it is the patentability of the final product per se which must be determined in a

"product by process" claim, and not the patentability of the process, and that an old or

obvious product produced by a new method is not patentable as a product, whether

claimed in "product by process" claims or not. Note that the applicant has the burden

of proof in such cases, as the above case law makes clear.

Regarding claim 2, APA teaches in figure 1 a guard ring pattern extending continuously

along the periphery of the substrate.

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Regarding claim 3, APA teaches in figure 1 a conductive pattern extending in the form of a straight line along peripheral edge of the substrate.

Regarding claim 4, the combination of Cook et al. and APA teach a conductive pattern changes a direction repeatedly and alternatively in the plane parallel in correspondence to the conductive wall.

Regarding claim 7 Chiang et al. teach in figure 25 an etch stop layer 390 interposed between the first and second insulation films. Therefore, the device of APA Chiang et al. teach an etch stop layer 390 interposed between the first and second insulation films, as claimed.

## Response to Arguments

3. Applicant argues on page 4 that elements 393 and 394 of Chiang et al. form a via plug and not a conductive wall extending continuously in the lateral direction.

Chiang et al. is not cited to teach the limitation of a conductive wall extending continuously in the lateral direction. Chiang et al. is cited to teach forming a conductive structure using etch stop layers. Chiang et al. teach in figure 25 a conductive layer 393, 394 (column 21, line 25) extending from a bottom principal surface of the interlayer insulation film

391 to a top principal surface thereof, and a second insulation film 323 (an etch stop layer) that supports conductive pattern 360, 361 laterally.

Papers related to this application may be submitted to Technology center (TC) 2800 by facsimile transmission. Papers should be faxed to TC 2800 via the TC 2800 Fax center located in Crystal Plaza 4, room 4-C23. The faxing of such papers must conform with the notice published in the Official Gazette, 1096 OG 30 (November 15, 1989). The Group 2811 Fax Center number is (703) 308-7722 and 308-7724. The Group 2811 Fax Center is to be used only for papers related to Group 2811 applications.

Any inquiry concerning this communication or any earlier communication from the Examiner should be directed to *Examiner Nadav* whose telephone number is **(703) 308-8138**. The Examiner is in the Office generally between the hours of 7 AM to 4 PM (Eastern Standard Time) Monday through Friday. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas, can be reached at **(703)** 308-2772.

Any inquiry of a general nature or relating to the status of this application should be directed to the **Technology Center Receptionists** whose telephone number is **308-0956** 

O.N. March 13, 2003 ORI NADAV
PATENT EXAMINER
TECHNOLOGY CENTER 2800

as No